

N-channel 100 V, 19 mΩ logic level MOSFET in LFPAK56 4 November 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100 % tested
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

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- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

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1.1.1

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	56	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	167	W
Static char	acteristics			,		
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
Dynamic cl	naracteristics					,
Q _{GD}	gate-drain charge	$I_{D} = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{Fig. 13}; \underline{Fig. 14}$	-	14.1	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UTA
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information										
Type number	Package									
	Name	Description	Version							
PSMN019-100YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669							

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN019-100YL	19L100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

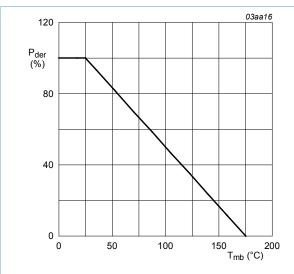
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	56	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	40	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3	-	226	А
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode					-
I _S	source current	T _{mb} = 25 °C		-	56	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	226	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & I_D = 56 \text{ A}; V_{sup} \leq 100 \text{V}; \text{R}_{\text{GS}} = 50 \Omega; \\ & $	[1][2]	-	94.1	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

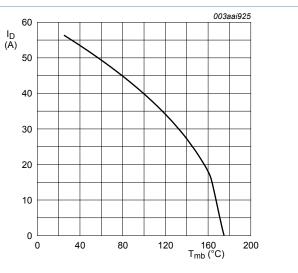
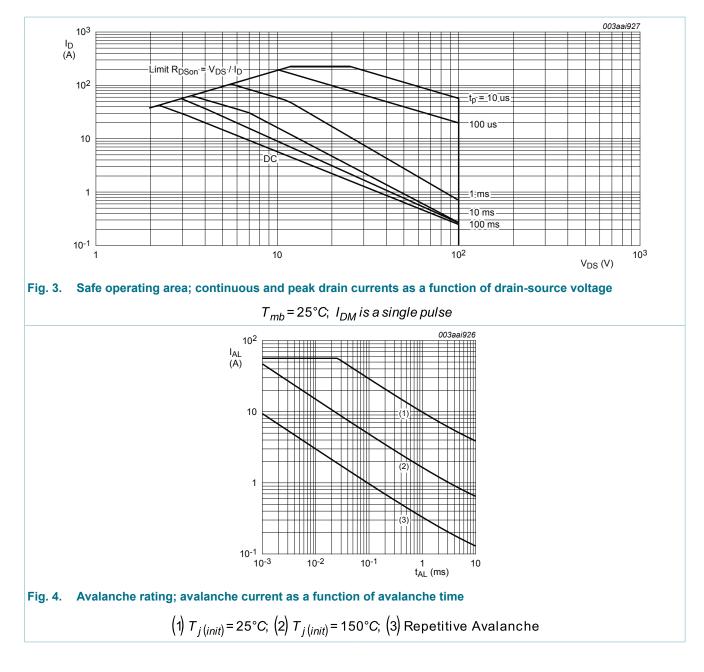


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$

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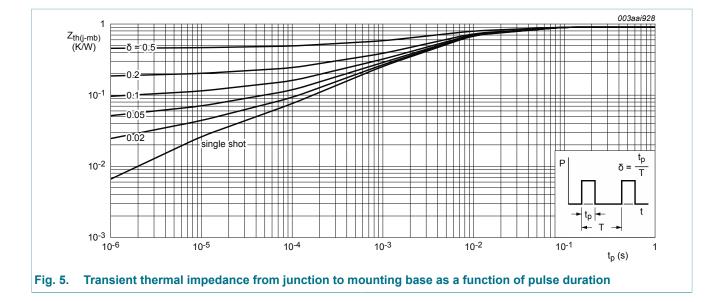
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.9	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				_
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
DSS drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.04	10	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	14.6	19	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	14	18	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	52.4	mΩ
Dynamic cl	naracteristics	· · ·				
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	72.4	-	nC
		I _D = 15 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	39	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	8.5	-	nC

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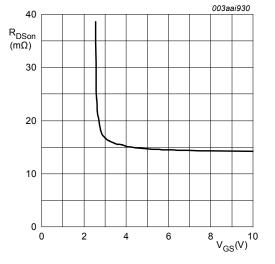
Symbol	Parameter	Conditions	I	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge			-	14.1	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;		-	3814	5085	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	222	266	pF
C _{rss}	reverse transfer capacitance			-	133	182	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_L = 5 Ω ; V_{GS} = 5 V;		-	18.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$		-	36.8	-	ns
t _{d(off)}	turn-off delay time			-	59.6	-	ns
t _f	fall time	-		-	34.3	-	ns
Source-dra	in diode						
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	38	-	ns

V_{DS} = 25 V; T_i = 25 °C

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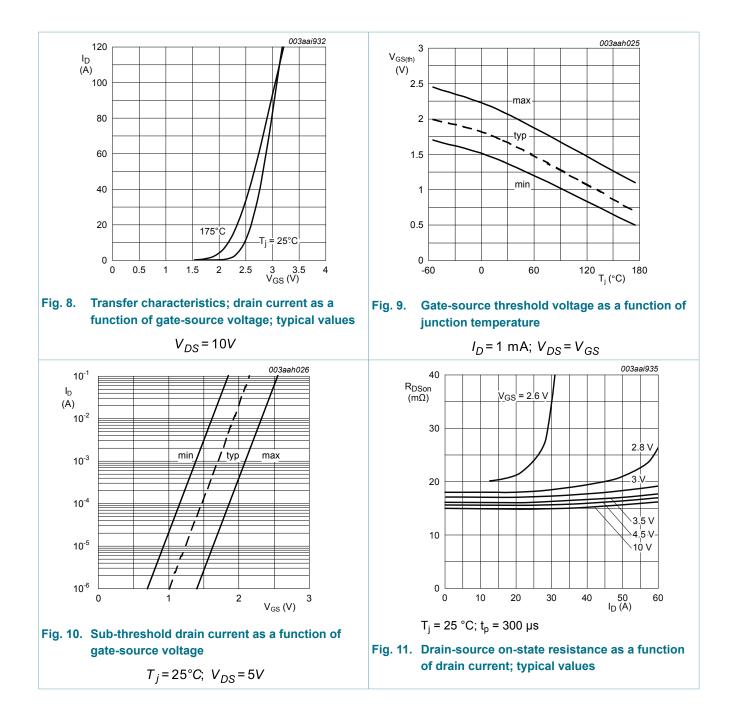


 $T_j = 25^{\circ}C; I_D = 15A$

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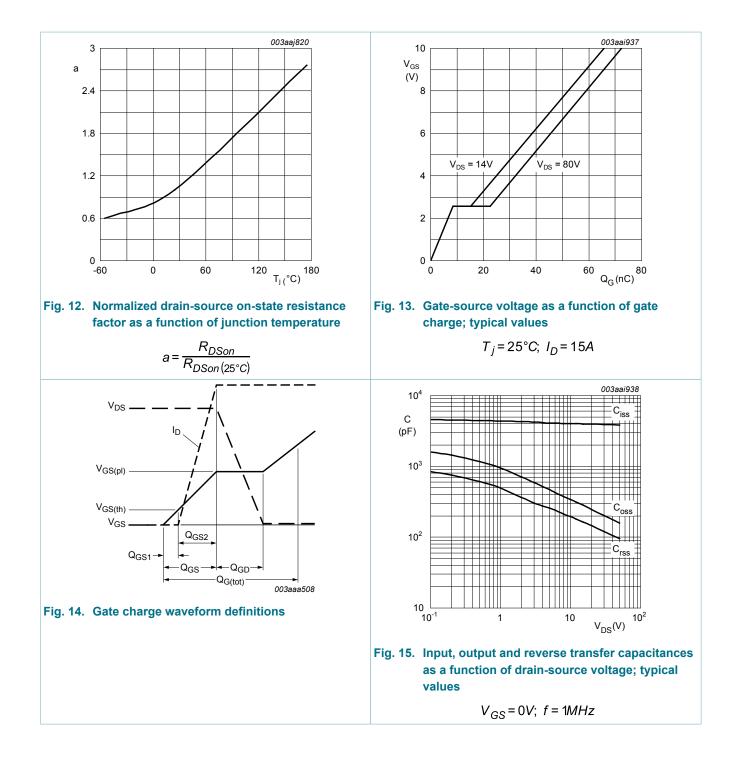
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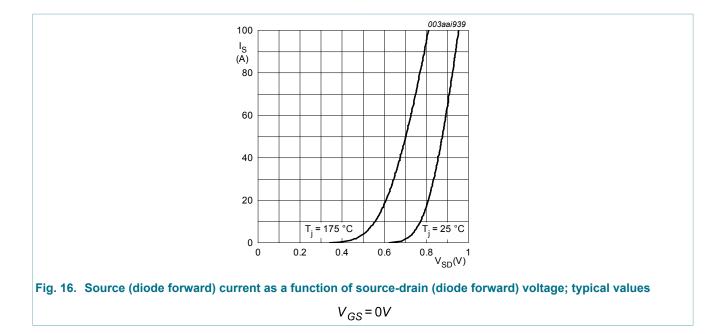
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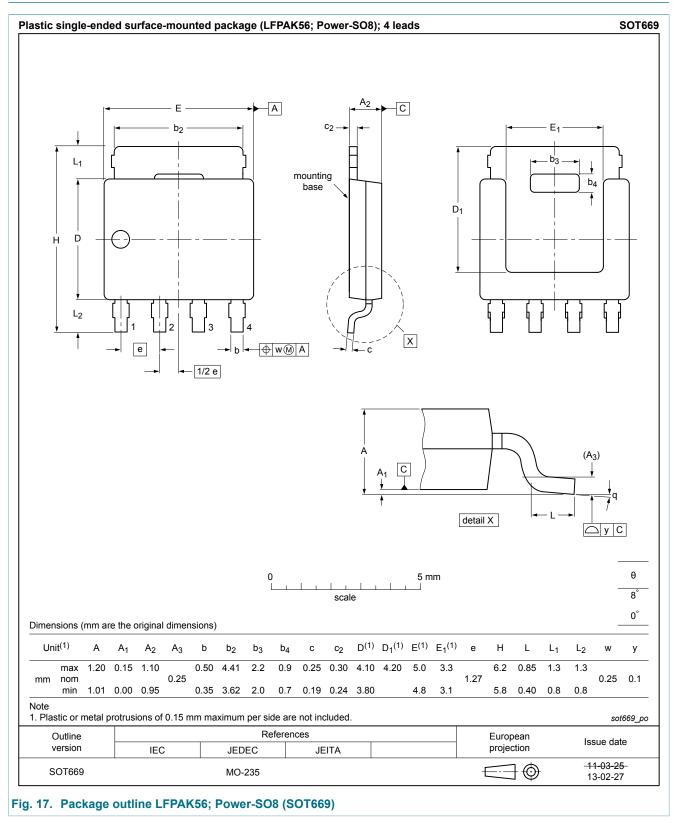
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11. Package outline



PSMN019-100YL

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